

UTC654

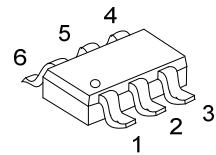
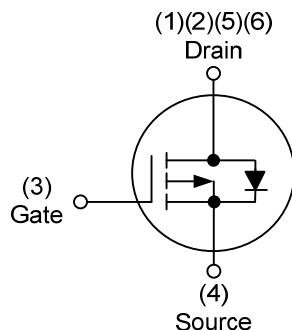
Power MOSFET

P-CHANNEL
ENHANCEMENT MODE

■ DESCRIPTION

As P-Channel Logic Level MOSFET, **UTC654** has been optimized for battery power management applications. And it's produced using UTC's advanced Power Trench process.

■ SYMBOL



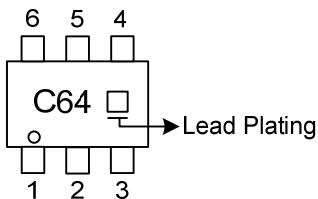
SOT-26

■ ORDERING INFORMATION

| Ordering Number | | Package | Pin Assignment | | | | | | Packing |
|-----------------|---------------|---------|----------------|---|---|---|---|---|-----------|
| Lead Free | Halogen Free | | 1 | 2 | 3 | 4 | 5 | 6 | |
| UTC654L-AG6-R | UTC654G-AG6-R | SOT-26 | D | D | G | S | D | D | Tape Reel |

| | | |
|---------------|---|--|
| UTC654L-AG6-R | (1)Packing Type (2)Package Type (3)Lead Plating | (1) R: Tape Reel (2) AG6: SOT-26 (3) G: Halogen Free, L: Lead Free |
|---------------|---|--|

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|-----------------------------------|-----------|------------|------------------|
| Drain-Source Voltage | V_{DSS} | -30 | V |
| Gate-Source Voltage | V_{GSS} | ± 20 | |
| Continuous Drain Current (Note 3) | I_D | -3.6 | A |
| Pulsed Drain Current (Note 2) | I_{DM} | -10 | |
| Power Dissipation | P_D | 1.6 | W |
| Junction Temperature | T_J | +150 | $^\circ\text{C}$ |
| Storage Temperature | T_{STG} | -55 ~ +150 | $^\circ\text{C}$ |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | MIN | TYP | MAX | UNIT |
|---------------------|---------------|-----|-----|-----|---------------------------|
| Junction-to-Ambient | θ_{JA} | 78 | | | $^\circ\text{C}/\text{W}$ |
| Junction-to-Case | θ_{JC} | 30 | | | $^\circ\text{C}/\text{W}$ |

■ ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise specified)

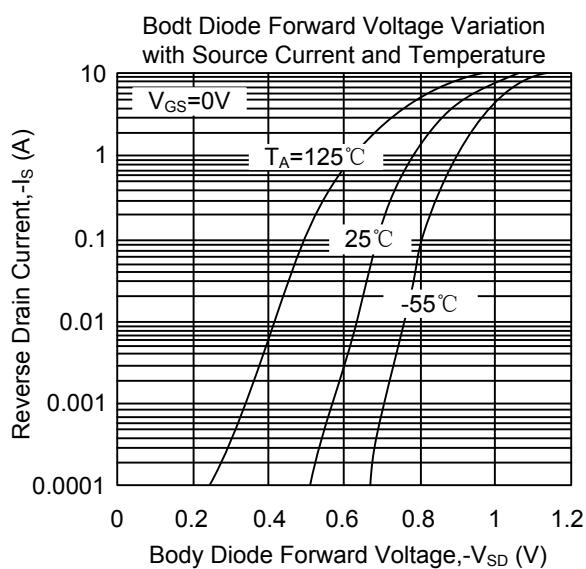
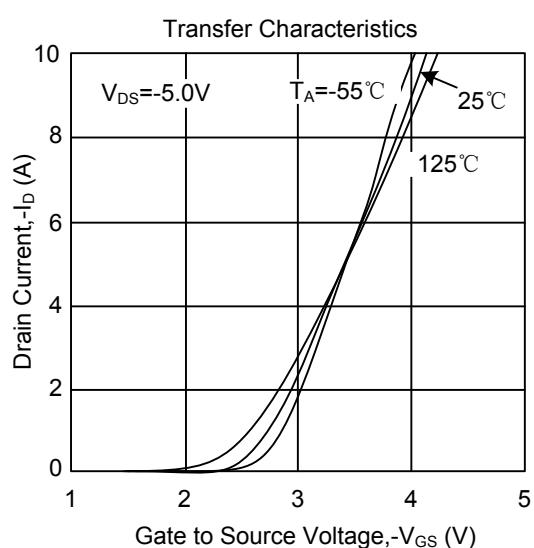
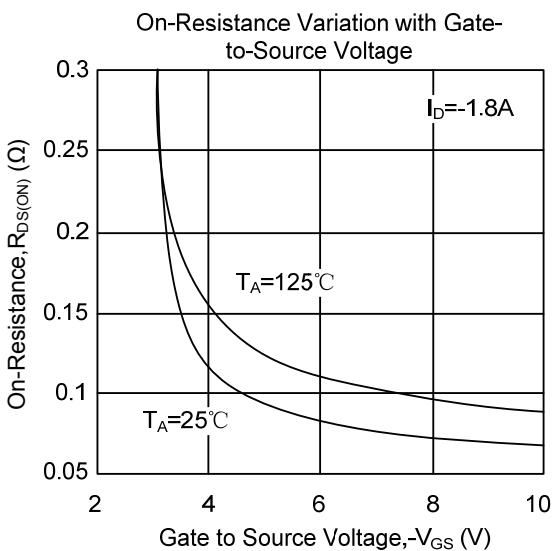
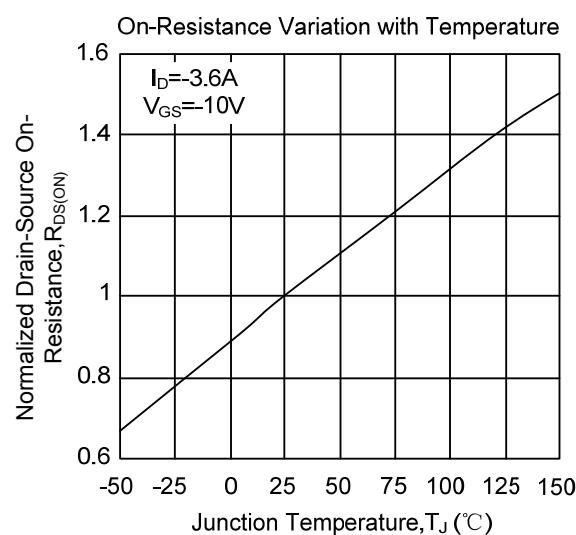
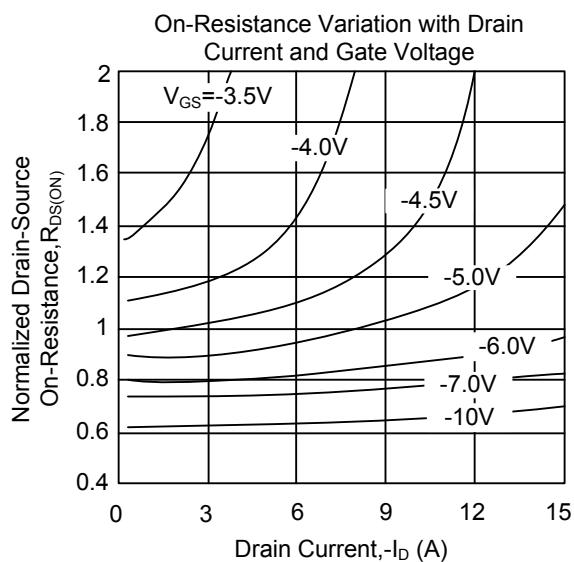
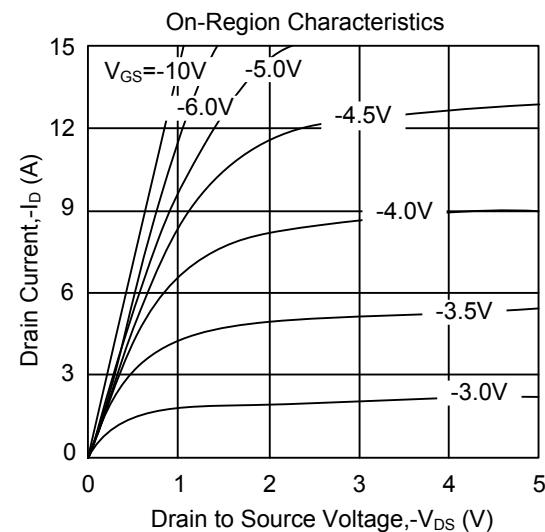
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--|------------------------------|--|-----|------|-----------|----------------------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0\text{V}, I_D = -250\text{ }\mu\text{A}$ | -30 | | | V |
| Drain-Source Leakage Current | I_{DSS} | $V_{DS} = -24\text{V}, V_{GS} = 0\text{ V}$ | | | -1 | μA |
| Gate-Source Leakage Current | I_{GSS} | $V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |
| Breakdown Voltage Temperature Coefficient | $\Delta BV_{DSS}/\Delta T_J$ | Referenced to $25^\circ\text{C}, I_D = -250\mu\text{A}$ | -22 | | | mV/C |
| ON CHARACTERISTICS | | | | | | |
| Gate-Threshold Voltage | $V_{GS(\text{TH})}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | -1 | -1.9 | -3 | V |
| Static Drain-Source On-Resistance (Note2) | $R_{DS(\text{ON})}$ | $V_{GS} = -10\text{ V}, I_D = -3.6\text{A}$ | | 63 | 75 | $\text{m}\Omega$ |
| | | $V_{GS} = -4.5\text{ V}, I_D = -2.7\text{A}$ | | 100 | 125 | |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{ISS} | $V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$ | | 298 | | pF |
| Output Capacitance | C_{OSS} | | | 83 | | |
| Reverse Transfer Capacitance | C_{RSS} | | | 39 | | |
| SWITCHING CHARACTERISTICS | | | | | | |
| Turn-ON Delay Time (Note2) | $t_{D(\text{ON})}$ | $V_{DD} = -15\text{V}, I_D = -1\text{A}, V_{GS} = -10\text{V}, R_{\text{GEN}} = 6\text{ }\Omega$ | | 6 | 12 | ns |
| Turn-ON Rise Time | t_R | | | 13 | 23 | |
| Turn-OFF Delay Time | $t_{D(\text{OFF})}$ | | | 11 | 20 | |
| Turn-OFF Fall-Time | t_F | | | 6 | 12 | |
| Total Gate Charge (Note2) | Q_G | $V_{DS} = -15\text{V}, V_{GS} = -10\text{V}, I_D = -3.6\text{ A}$ | | 6.2 | 9 | nC |
| Gate-Source Charge | Q_{GS} | | | 1 | | |
| Gate-Drain Charge | Q_{GD} | | | 1.2 | | |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS | | | | | | |
| Drain-Source Diode Forward Voltage | V_{SD} | $V_{GS} = 0\text{V}, I_S = -1.3\text{ A}$ (Note 2) | | -0.8 | -1.2 | V |
| Maximum Continuous Drain Source Diode Forward Current | I_S | | | | -1.3 | A |

Notes: 1. Pulse width limited by $T_{J(\text{MAX})}$

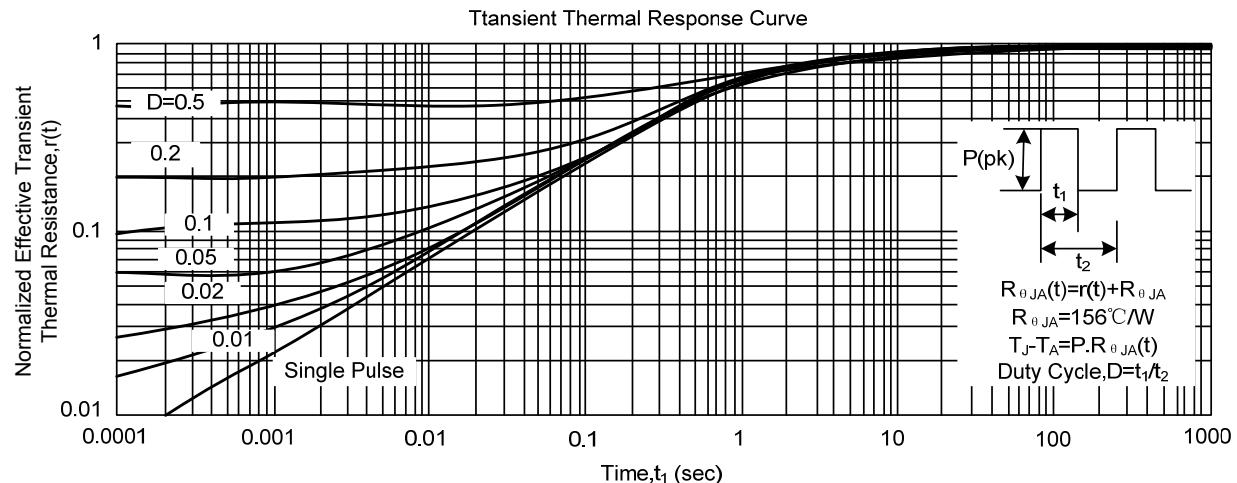
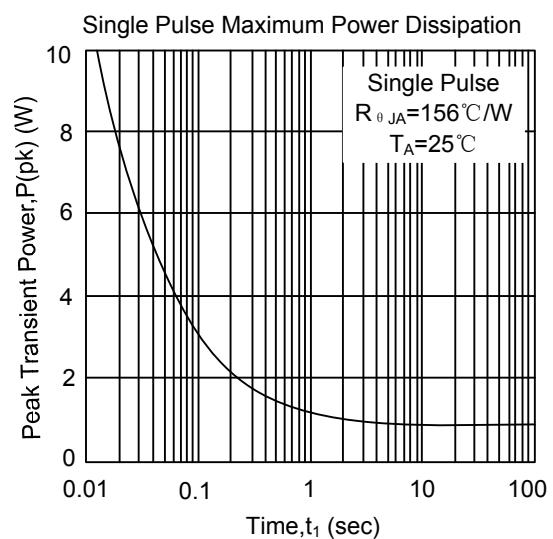
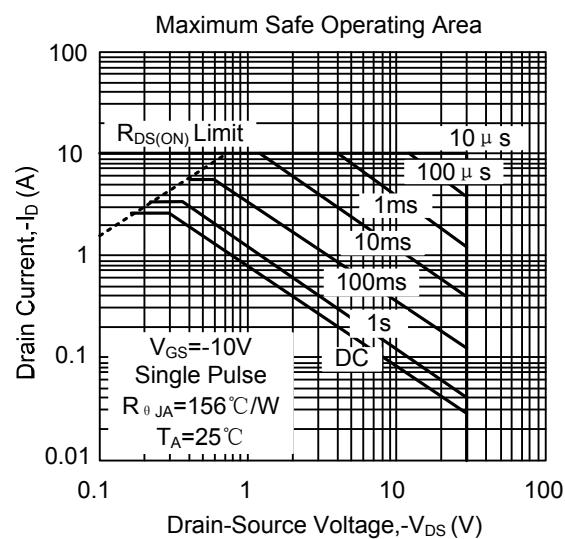
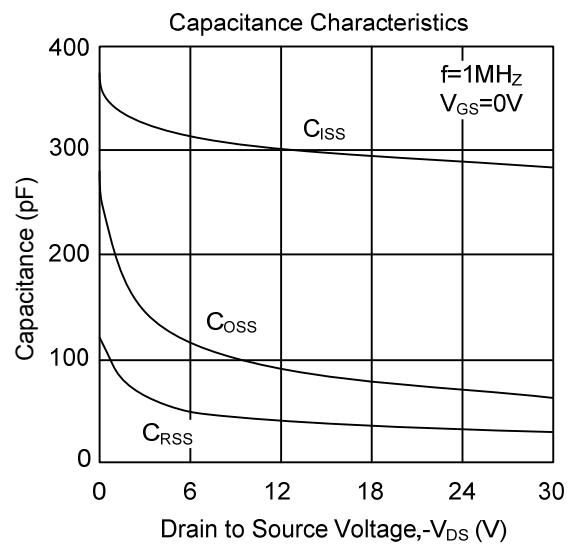
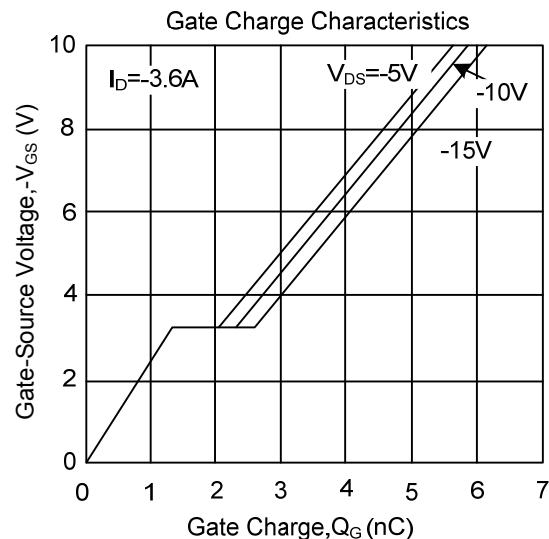
2. Pulse width $\leq 300\text{us}$, duty cycle $\leq 2\%$.

3. Surface mounted on 1 in² copper pad of FR4 board; $270^\circ\text{C}/\text{W}$ when mounted on min.

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS



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